WHAT IS CLAIMED IS:

1. A Schottky contact structure, comprising:

a Schottky contact, comprising:

a plurality of stacks of metal layers, each one the stacks, comprising:

a first layer of a first metal; and

a second layer of a second metal on the first layer;

wherein the first metal of the first layer of a first one of the plurality of stacks is in Schottky contact with a semiconductor; and

an electrode for the Schottky contact disposed on the Schottky contact, the electrode having a third metal, the third metal is in direct contact with the second metal of the second layer of an upper most one of the plurality of stacks of metal layers.

2. The Schottky contact structure recited in claim 1 and wherein the second metal provides a barrier against migration between the third metal and the first metal.

3. The Schottky contact structure recited in claim 1 wherein the first metal is nickel; the second metal is platinum; and the third metal is gold.

4. The Schottky contact structure recited in claim 1 wherein the second metal of the second layer is in direct contact with the first metal of the first layer.

5. The Schottky contact structure recited in claim 4 wherein the first metal of a third layer is in direct contact with the second metal of a fourth layer;

wherein the third layer is the first layer of a second one of the plurality of stacks; and

wherein the fourth layer is the second layer of the second one of the plurality of stacks.

6. The Schottky contact structure recited in claim 4 wherein the first metal of a fifth layer is in direct contact with the second metal of the fourth layer, wherein the fifth layer is the first layer of a third one of the plurality of stacks.

7. The Schottky contact structure recited in claim 6 wherein first metal of the fifth layer is in direct contact with the second metal of a sixth layer, wherein the sixth layer is the second layer of the third one of the plurality of stacks.

8. A Schottky contact structure, comprising:

a Schottky contact comprising:

a first layer of a first metal in Schottky contact with a semiconductor;

a second layer of a second metal on the first layer;

a third layer of the first metal on the second layer;

a fourth layer of the second metal on the third layer; and

an electrode for the Schottky contact structure disposed on the Schottky contact, the electrode having a third metal, the second metal providing a barrier against migration between the third metal and the first metal;

wherein the second metal of the second layer is in direct contact with the first metal of the first layer;

wherein the first metal of the third layer is in direct contact with the second metal of the second layer;

wherein the second metal of the fourth layer is in direct contact with the first metal of the third layer;

wherein the first metal of a fifth layer is in direct contact with the second metal of the fourth layer;

wherein the second metal of a sixth layer is in direct contact with the first metal of the fifth layer;

wherein the third metal of the electrode is in direct contact with the second metal of the sixth layer; and

wherein the first metal is nickel; the second metal is platinum; and the third metal is gold.

9. A Schottky contact structure, comprising:

a Schottky contact in Schottky contact with a semiconductor, the Schottky contact comprising a plurality of stacks, each one of the stacks comprising a lower layer of Ni and upper layer of Pt; and

wherein the Ni is in direct contact with the Pt; and including an electrode on the Schottky contact.

10. The Schottky contact structure recited in claim 9 wherein the electrode comprises a layer of gold on the Ni of an upper one of the plurality of stacks.

11. The Schottky contact structure recited in claim 10 and wherein the layer of gold is in direct contact with the Pt of the upper one of the plurality of stacks.

12. A Field Effect Transistor, comprising:

a source;

a drain;

a gate electrode structure disposed between the source and the drain for controlling a flow of carriers between the source and the drain, the gate electrode structure, comprising:

a Schottky contact, comprising:

a plurality of stacks of metal layers, each one the stacks, comprising:

a first layer of a first metal; and

a second layer of a second metal on the first layer;

wherein the first metal of the first layer of a first one of the plurality of stacks is in Schottky contact with a semiconductor; and

an electrode for the Schottky contact an structure disposed on the Schottky contact, the electrode having a third metal, the electrode having a third metal in direct contact with the second metal of the second layer of an upper most one of the plurality of stacks of metal layers.

13. The Field Effect Transistor recited in claim 12 wherein the second metal provides a barrier against migration between the third metal and the first metal.